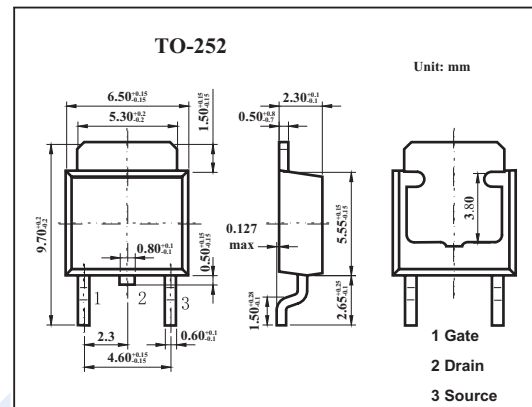


Silicon N-Channel MOSFET

2SK2329S

■ Features

- Low on-resistance
- High speed switching
- Low drive current
- 2.5 V gate drive device can be driven from 3 V source
- Suitable for Switching regulator, DC-DC converter



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Drain to source voltage	V _{DSS}	30	V
Gate to source voltage	V _{GSS}	±10	V
Drain current	I _D	10	A
	I _{dp} *	40	A
Power dissipation	P _D	20	W
Channel temperature	T _{ch}	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

* PW ≤ 10 μs, Duty Cycle ≤ 1%

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Drain to source breakdown voltage	V _{DSS}	I _D =10mA, V _{GS} =0	30			V
Gate to source voltage	V _{GSS}	I _G =±200 μA, V _{GS} =0	±10			V
Drain cut-off current	I _{DSS}	V _{DS} =25V, V _{GS} =0			100	μA
Gate leakage current	I _{GSS}	V _{GS} =±6.5V, V _{DS} =0			±10	μA
Gate to source cutoff voltage	V _{GS(off)}	V _{DS} =10V, I _D =1mA	0.4		1.4	V
Forward transfer admittance	Y _{fs}	V _{DS} =10V, I _D =5A	10	18		S
Drain to source on-state resistance	R _{DS(on)}	V _{GS} =4V, I _D =5A		0.03	0.04	Ω
		V _{GS} =2.5V, I _D =5A		0.04	0.06	Ω
Input capacitance	C _{iss}	V _{DS} =10V, V _{GS} =0, f=1MHZ		1250		pF
Output capacitance	C _{oss}			540		pF
Reverse transfer capacitance	C _{rss}			120		pF
Turn-on delay time	t _{on}	I _D =5A, V _{GS(on)} =4V, R _L =2 Ω		20		ns
Rise time	t _r			145		ns
Turn-off delay time	t _{off}			225		ns
Fall time	t _f			125		ns